

BYC8MB-650P

# Hyperfast power diode

Rev.01 - 08 October 2023

**Product data sheet** 

#### **1. General description**

Hyperfast power diode in a TO263 plastic package.



#### 2. Features and benefits

- Low leakage current
- · Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

#### 3. Applications

- Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

#### 4. Quick reference data

|                  | uick reference data                    | o   |       |        |      |      |      |  |
|------------------|--|---|-------|--------|------|------|------|--|
| Symbol           | Parameter                              | Conditions  | Notes | Values |      |      | Unit |  |
| Absolute         | maximum rating                         |   |       |        |      |      |      |  |
| $V_{RRM}$        | repetitive peak reverse voltage        |   |       |        | 650  |      | V    |  |
| $I_{F(AV)}$      | average forward current                | δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 127 °C;<br>Fig. 1; Fig. 2; Fig. 3                                      |       | 8      |      | А    |      |  |
| I <sub>FRM</sub> | repetitive peak forward current        | δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 127 °C;<br>square-wave pulse                                      |       | 16     |      |      | A    |  |
| $I_{\text{FSM}}$ | non-repetitive peak<br>forward current | $t_{p}$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br><u>Fig. 4</u>   |       | 91     |      |      | A    |  |
|                  |  | $t_{\text{p}}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse  |       |        |      | А    |      |  |
| Symbol           | Parameter                              | Conditions  | Notes | Min    | Тур  | Max  | Unit |  |
| Static ch        | aracteristics                          |   |       |        |      |      |      |  |
| V <sub>F</sub>   | forward voltage                        | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   |       | -      | 2.20 | 3.20 | V    |  |
|                  |  | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  |       | -      | 1.45 | 2.45 | V    |  |
| Dynamic          | characteristics                        |   |       |        |      |      |      |  |
| t <sub>rr</sub>  | reverse recovery time                  | I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs;<br>T <sub>i</sub> = 25 °C; <u>Fig. 7</u> |       | -      | 13   | -    | ns   |  |

## **5. Pinning information**

| Table 2. F | Pinning infor | mation                             |                    |                             |
|------------|---------------|------------------------------------|--------------------|-----------------------------|
| Pin        | Symbol        | Description                        | Simplified outline | Graphic symbol              |
| 1          | nc            | no connected                       |                    |                             |
| 2          | К             | cathode [1]                        |                    | К <u>– Ң</u> А<br>001ааа020 |
| 3          | А             | anode                              | 0                  |                             |
| mb         | mb            | mounting base; connected to cathod |                    |                             |

[1] It is not possible to connect to pin 2 of the TO-263 package.

## 6. Ordering information

| Table 3. Ordering information |         |                       |         |               |         |             |  |  |
|-------------------------------|---------|-----------------------|---------|---------------|---------|-------------|--|--|
| Type number                   | Package | Orderable part number | Packing | Small packing | Package | Package     |  |  |
|                               | name    |                       | method  | quantity      | version | issue date  |  |  |
| BYC8MB-650P                   | TO263   | BYC8MB-650PJ          | Reel    | 800           | TO263d  | 17-Mar-2023 |  |  |

### 7. Marking

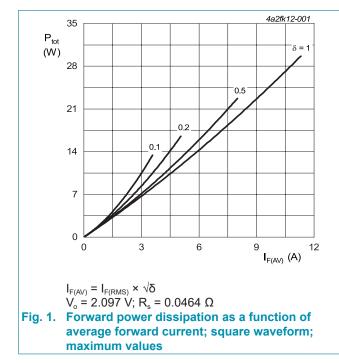
| Table 4. Marking codes |                |
|------------------------|----------------|
| Type number            | Marking codes  |
| BYC8MB-650P            | BYC8MB<br>650P |

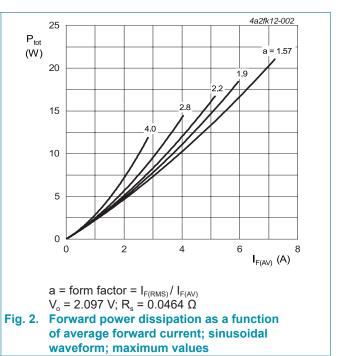
#### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

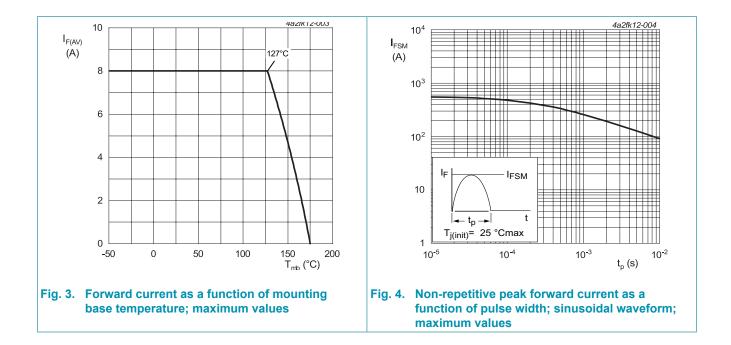
| Symbol             | Parameter                              | Conditions   | Notes | Values     | Unit |
|--------------------|--|--|-------|------------|------|
| V <sub>RRM</sub>   | repetitive peak reverse voltage        |  |       | 650        | V    |
| V <sub>RWM</sub>   | crest working reverse voltage          |  |       | 650        | V    |
| V <sub>R</sub>     | reverse voltage                        | DC   |       | 650        | V    |
| I <sub>F(AV)</sub> | average forward current                | δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 127 °C;<br>Fig. 1; Fig. 2; Fig. 3     |       | 8          | A    |
| I <sub>FRM</sub>   | repetitive peak forward<br>current     | $\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 127 °C; square-wave pulse |       | 16         | A    |
| I <sub>FSM</sub>   | non-repetitive peak<br>forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4                     |       | 91         | A    |
|                    |  | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                               |       | 100        | А    |
| T <sub>stg</sub>   | storage temperature                    |  |       | -65 to 175 | °C   |
| Tj                 | junction temperature                   |  |       | -65 to 175 | °C   |





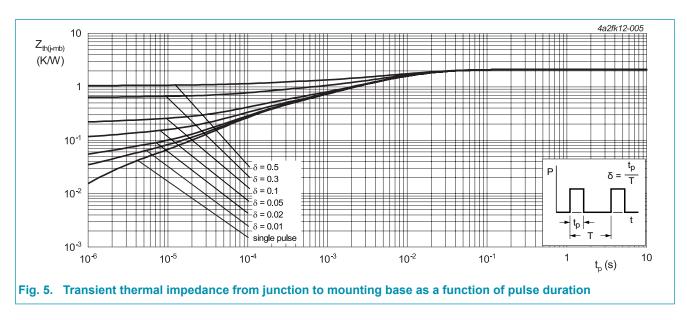
Hyperfast power diode

BYC8MB-650P



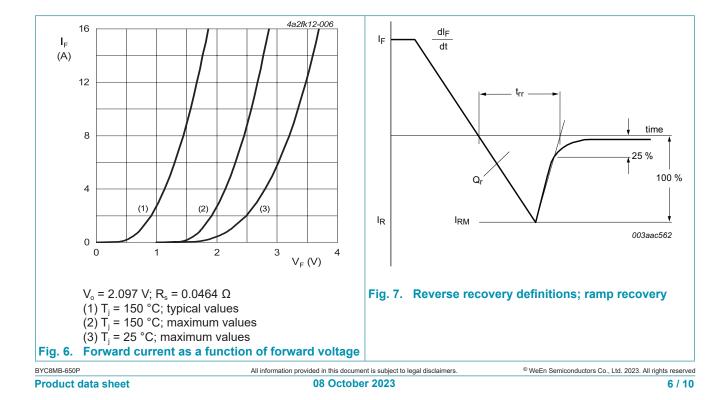
### 9. Thermal characteristics

| Symbol                | Parameter  | Conditions    | Notes | Min | Тур | Max | Unit |
|-----------------------|--|---------------|-------|-----|-----|-----|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance<br>from junction to<br>mounting base    | <u>Fig. 5</u> |       | -   | -   | 2.1 | K/W  |
| $R_{\text{th(j-a)}}$  | thermal resistance<br>from junction to<br>ambient free air | in free air   |       | -   | 60  | -   | K/W  |

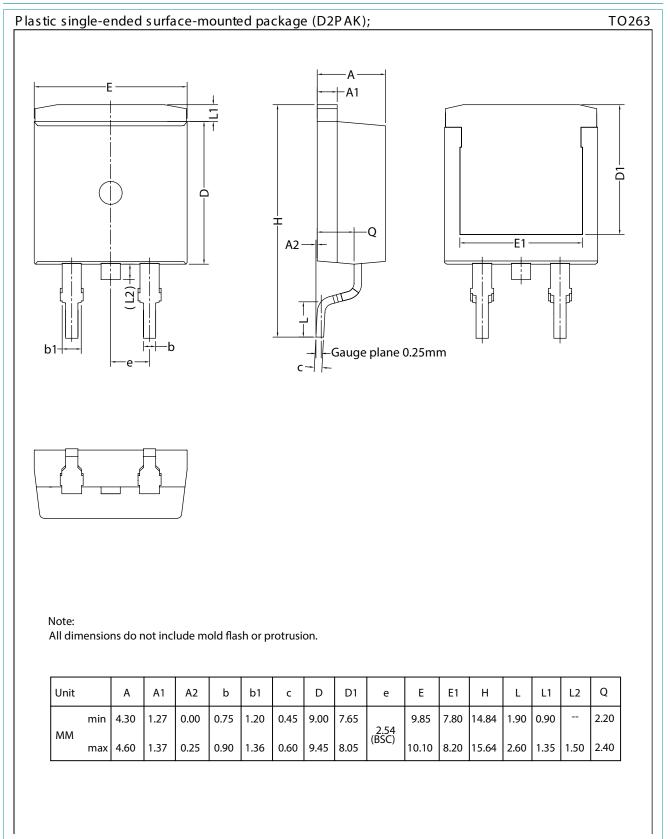


#### **10. Characteristics**

| Symbol                        | Parameter                                   | Conditions  | Notes | Min  | Тур  | Max  | Unit |
|-------------------------------|---|---|-------|------|------|------|------|
| Static ch                     | aracteristics                               |   |       |      |      |      |      |
| V <sub>F</sub>                | forward voltage                             | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   |       | -    | 2.20 | 3.20 | V    |
|                               |   | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  |       | -    | 1.45 | 2.45 | V    |
| I <sub>R</sub>                | reverse current                             | V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C  |       | -    | 0.6  | 30   | μA   |
|                               |   | V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C   |       | -    | 0.07 | 0.8  | mA   |
| Dynamic                       | characteristics                             | 1   |       | 1    |      |      | 1    |
| Q <sub>r</sub> reverse charge | reverse charge                              | $I_F = 8 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; \text{ Fig. 7}$      |       | -    | 38   | -    | nC   |
|                               |   | I <sub>F</sub> = 8 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs;<br>T <sub>j</sub> = 125 °C; <u>Fig. 7</u>                     |       | -    | 93   | -    | nC   |
| T <sub>rr</sub> reverse r     | reverse recovery time                       | $I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{RR} = 0.25 \text{ A}; T_j = 25 \text{ °C}$  |       | -    | 20   | -    | ns   |
|                               |   | I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                       |       | -    | 13   | -    | ns   |
|                               |   | I <sub>F</sub> = 8 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                      |       | -    | 28   | -    | ns   |
|                               |   | I <sub>F</sub> = 8 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs;<br>T <sub>j</sub> = 125 °C; <u>Fig. 7</u>                     |       | -    | 45   | -    | ns   |
| currentnon-r                  | peak reverse recovery currentnon-repetitive | I <sub>F</sub> = 8 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                      |       | -    | 2.7  | -    | A    |
|                               | avalanche energy                            | $I_F = 8 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$<br>$T_j = 125 ^\circ\text{C}; \text{ Fig. 7}$ |       | -    | 4.2  | -    | A    |
| E <sub>as</sub>               | non-repetitive<br>avalanche energy          | T <sub>j(init)</sub> = 25 °C  |       | 10.8 | -    | -    | mJ   |



### **11. Package outline**



# BYC8MB-650P

#### Hyperfast power diode

### 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product<br>status [3] | Definition  |
|--------------------------------------|-----------------------|---|
| Objective<br>[short] data<br>sheet   | Development           | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production            | This document contains the product specification.   |

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